## SILICON EPITAXIAL PLANAR SWITCHING DIODE

## Application

• Ultra high speed switching





SOT-323 Plastic Package Marking Code: **PH** 

## <u>Absolute Maximum Ratings ( $T_a = 25 \text{ °C}$ )</u>

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V <sub>RM</sub>	80	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Forward Current	Ι <sub>ο</sub>	100	mA
Maximum Peak Forward Current	I <sub>FM</sub>	300	mA
Surge Current (t = 1 µs)	I <sub>FSM</sub>	4	А
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

## Characteristics at T<sub>a</sub> = 25 °C

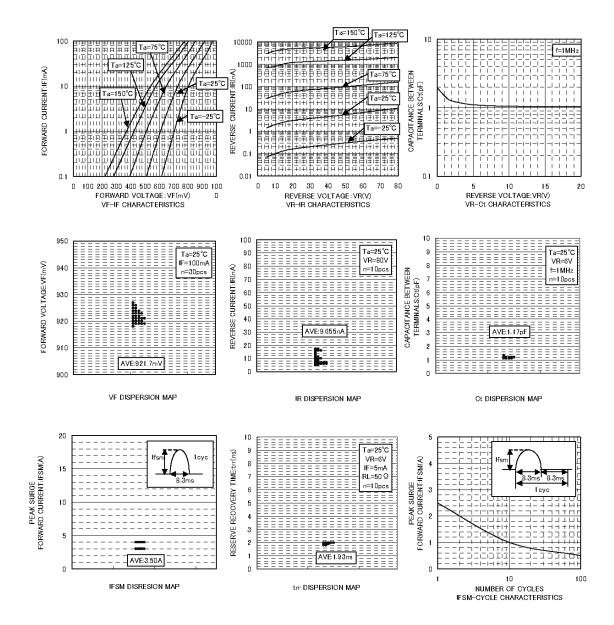
Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	1.2	V
Reverse Current at V <sub>R</sub> = 70 V	I <sub>R</sub>	0.1	μA
Total Capacitance at V <sub>R</sub> = 6 V, f = 1 MHz	CT	3.5	pF
Reverse Recovery Time at $V_R$ = 6 V, $I_F$ = 5 mA, $R_L$ = 50 $\Omega$	t <sub>rr</sub>	4	ns







Dated : 10/10/2008







ubsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 10/10/2008